



SHEET 1 OF 1

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Substitute for form 1449/PTO)

ATTY. DOCKET NO.
071971-0557SERIAL NO.
10/576,518APPLICANT
Tohru YAMAOKA, et al.FILING DATE
April 20, 2006GROUP
2614**U.S. PATENT DOCUMENTS**

| EXAMINER'S INITIALS | CITE NO. | Document Number Number-Kind Code ² (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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| EXAMINER'S INITIALS | CITE NO. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. |
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EXAMINER

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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